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PTO/SB/21 (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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TRANSMITTAL FORM (to be used for all correspondence after initial filing)	Application Number	09/699,466	
	Filing Date	October 31, 2000	
	First Named Inventor	Shunpei YAMAZAKI et al.	
	Group Art Unit	2813	
	Examiner Name	Asok SARKAR	
Total Number of Pages in This Submission		Attorney Docket Number	740756-2222

ENCLOSURES (check all that apply)		
<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s)	<input type="checkbox"/> After Allowance Communication to Group RECEIVED JUL 10 2001 TECHNOLOGY CENTER 2800
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SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT	
Firm or Individual name	<u>Luan C. Do</u> Nixon Peabody LLP 8180 Greensboro Drive Suite 800 McLean, VA 22012
Signature	
Date	July 5, 2001

CERTIFICATE OF MAILING		
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231 on this date: <u>7-5-2001</u>		
Type or printed name	<u>SHIRLEY B. STRAIN</u>	
Signature	<u>Shirley B. Strain</u>	Date <u>7-5-01</u>

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IDS
PATENT
740756-002212
7/12/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI et al.

Application No.: 09/699,466

Filed: October 31, 2000

For: METHOD FOR FABRICATING A
SEMICONDUCTOR DEVICE

Art Unit: 2813

Examiner: Asok SARKAR

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**REQUEST FOR CORRECTION OF PRIOR
INFORMATION DISCLOSURE STATEMENT**

Commissioner of Patents
Washington, D.C. 20231

July 5, 2001

Dear Sir:

Supplemental to the Information Disclosure Statement filed October 31, 2000, attached hereto is corrected page 6 of Form PTO-1449 to be made of record in the above-identified application. Upon further review of the application, the undersigned noticed three typographical errors in the listings of three separate references listed below for which Abstracts had been submitted for each:

1. JP 61-63107 published 4/1/86
2. JP 7-16134 published 6/23/95
3. JP 52-99348 published 11/93

Each corrected reference number has been listed in boldtype on the Form PTO-1449 sheet for the Examiner's convenience. Applicants apologize for the inconvenience caused by these errors.

It is requested that this Request For Corrected Information Disclosure Statement be considered and made of record in the above-captioned application. It is respectfully requested that an Examiner-initialed copy of this form be returned to the undersigned. In particular, the

Application No.: 09/699,466
Art Unit: 2823

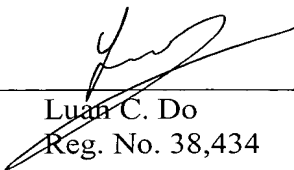
Attorney Docket No.: 740756-2018
Page 2

Examiner is requested to consider U.S. Patent No. 5,531,182 listed on page 5 of the PTO-1449 form submitted on October 31, 2000.

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 19-2380.

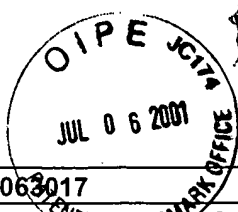
Respectfully submitted,

By


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EJR/LCD:sbs



09/699,466

61-063017	04/01/86	Japan	Abstract
3-280420 (Japanese & English)	12/11/91	Japan	Full
5-82442	04/02/93	Japan	Abstract
7-161634	06/23/95	Japan	Abstract
2-140915	05/20/90	Japan	Full
1-206632	08/18/89	Japan	Abstract
5-299348	11/93	Japan	Abstract
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6-0105216	10/06/85	Japan	Full
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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